

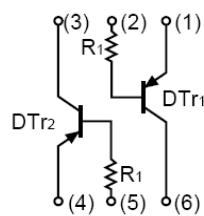
General purpose transistors (dual transistors)

FEATURES

- Two DTA143T chips in a package
- Mounting possible with SOT-363 automatic mounting machines.
- Transistor elements are independent, eliminating interference.
- Mounting cost and area be cut in half.

Marking: B3

Equivalent circuit



Absolute maximum ratings(Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{(BR)CBO}$	-50	V
Collector-emitter voltage	$V_{(BR)CEO}$	-50	V
Emitter-base voltage	$V_{(BR)EBO}$	-5	V
Collector current	I_C	-100	mA
Collector Power	P_C	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~150	°C

Electrical characteristics (Ta=25°C)

Parameter	Symb	Min	Typ	Max	Unit	Conditions
Collector-base breakdown voltage	$V_{(BR)CB}$	-50			V	$I_C=-50\mu A$
Collector-emitter breakdown voltage	$V_{(BR)CE}$	-50			V	$I_C=-1mA$
Emitter-base breakdown voltage	$V_{(BR)EB}$	-5			V	$I_E=-50\mu A$
Collector cut-off current	I_{CBO}			-0.5	μA	$V_{CB}=-50V$
Emitter cut-off current	I_{EBO}			-0.5	μA	$V_{EB}=-4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$			-0.3	V	$I_C=-5mA, I_B=-0.25mA$
DC current transfer ratio	h_{FE}	100		600		$V_{CE}=-5V, I_C=-1mA$
Input resistance	R_1	3.29	4.7	6.11	KΩ	
Transition frequency	f_T			250	MHz	$V_{CE}=-10V, I_E=5mA, f=100$

